

Jay Mody

List of Publications by Year in descending order

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23
papers

412
citations

933447

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1058476

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docs citations

24
times ranked

372
citing authors

#	ARTICLE	IF	CITATIONS
1	Mapping Conductance and Carrier Distributions in Confined Three-Dimensional Transistor Structures. <i>Nanoscience and Technology</i> , 2019, , 71-106.	1.5	3
2	Dopant/carrier profiling for 3D-structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 121-129.	0.8	23
3	Subnanometer Characterization of Nanoelectronic Devices. , 2013, , 677-704.		5
4	Atom Probe Tomography for 3D-dopant analysis in FinFET devices. , 2012, , .		4
5	Scanning spreading resistance microscopy for carrier profiling beyond 32nm node. , 2012, , .		1
6	Understanding device performance by incorporating 2D-carrier profiles from high resolution scanning spreading resistance microscopy into device simulations. <i>Solid-State Electronics</i> , 2012, 74, 38-42.	1.4	4
7	Two-dimensional carrier mapping at the nanometer-scale on 32nm node targeted p-MOSFETs using high vacuum scanning spreading resistance microscopy. <i>Solid-State Electronics</i> , 2012, 71, 69-73.	1.4	18
8	3D-carrier profiling in FinFETs using scanning spreading resistance microscopy. , 2011, , .		15
9	Non-Destructive Characterization of Activated Ion-Implanted Doping Profiles Based on Photomodulated Optical Reflectance. , 2011, , .		0
10	Atom-probe for FinFET dopant characterization. <i>Ultramicroscopy</i> , 2011, 111, 535-539.	1.9	51
11	Dopant and carrier profiling for 3D-device architectures. , 2011, , .		5
12	High performance n-MOS finFET by damage-free, conformal extension doping. , 2011, , .		6
13	Understanding device performance by incorporating 2D-carrier profiles from high resolution scanning spreading resistance microscopy into device simulations. , 2011, , .		0
14	Observation of diameter dependent carrier distribution in nanowire-based transistors. <i>Nanotechnology</i> , 2011, 22, 185701.	2.6	42
15	Two-dimensional carrier mapping at the nanometer-scale on 32nm node targeted p-MOSFETs using high vacuum scanning spreading resistance microscopy. , 2011, , .		0
16	Analysis and modeling of the high vacuum scanning spreading resistance microscopy nanocontact on silicon. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2010, 28, 401-406.	1.2	39
17	Experimental studies of dose retention and activation in fin field-effect-transistor-based structures. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2010, 28, C1H5-C1H13.	1.2	26
18	Dopant and carrier profiling in FinFET-based devices with sub-nanometer resolution. , 2010, , .		11

#	ARTICLE	IF	CITATIONS
19	Physical degradation of gate dielectrics induced by local electrical stress using conductive atomic force microscopy. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	17
20	Evolution of metastable phases in silicon during nanoindentation: mechanism analysis and experimental verification. <i>Nanotechnology</i> , 2009, 20, 305705.	2.6	109
21	Impact of the environmental conditions on the electrical characteristics of scanning spreading resistance microscopy. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 338.	1.3	13
22	Toward extending the capabilities of scanning spreading resistance microscopy for fin field-effect-transistor-based structures. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 351.	1.3	11
23	Scanning Spreading Resistance Microscopy For 3D-Carrier Profiling in FinFET-based Structures. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1070, 1.	0.1	3